100V N-Ch Power MOSFET

V_{DS}		100	V
$R_{DS(on),typ}$	V_{GS}=10V	22.0	m
$R_{DS(on),typ}$			

Gate to Source Voltage V_{GS} -

P_D T_c

Max

Electrical Characteristics at T_j=25 (unless otherwise specified)

Static Characteristics

Parameter	Symbol	Conditions	Value min	Value typ	Value max	Unit
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250 A	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250 A	1.4	2	2.4	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=100V, T_j=25	-	-	1	A
		V_{GS}=0V, V_{DS}=100V, T_j=100	-	-	100	
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	10θ	±100	nA
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=8A	-	22	29	m
		V_{GS}=4.5V, I_D=6A	-	26	36	
Transconductance						

Dynamic Characteristics

Input CapacV 0.001265wm[I)-7(nput)-7( )1(C)7T

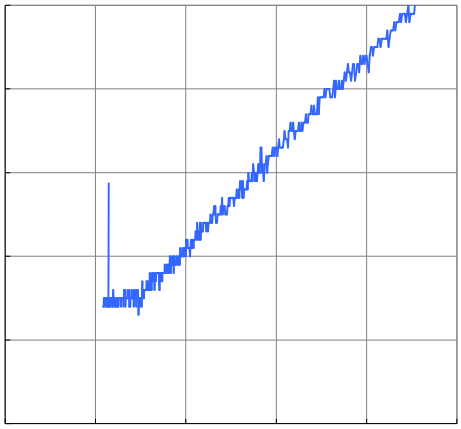
Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage	Figure 8. Typical Capacitance vs. Drain-to-Source Voltage
	

Figure 9. Maximum Safe Operating Area	Figure 10. Maximun Drain Current vs. Case Temperature

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

Inductive switching Test

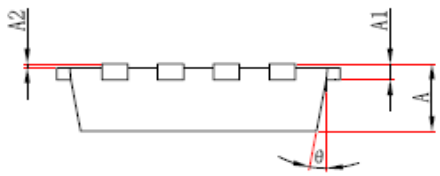
Gate Charge Test

Uclamped Inductive Switching (UIS) Test

Diode Recovery Test

Package Outline

DFN3.3*3.3_P, 8 Leads



Side View